PNP Silicon Epitaxial Planar Transistor

for switching and interface circuit and
drive circuit applicatio

Resistor Values

Type	R1 (K)	R2 (K)
MMUN2111	10	10

Absolute Maximum Ratings (Ta = 25°C)

Characteristics at Ta = 25°C

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain					
at $-V_{CE}$ = 10 V, $-I_C$ = 5 mA	MMUN2111	h_{FE}	35	-	-
	MMUN2112	h_{FE}	60	-	-
	MMUN2113	h_{FE}	80	-	-
	MMUN2114	h_{FE}	80	-	-
	MMUN2115	h_{FE}	160	-	-
	MMUN2116	h_{FE}	160	-	-
	MMUN2130	h_{FE}	3	-	-
	MMUN2131	h_{FE}	8	-	-
	MMUN2132	h_{FE}	15	-	-
	MMUN2133	h_{FE}	80	-	-
	MMUN2134	h_{FE}	80	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 50 V		CBO	-	100	nA
Collector Emitter Cutoff Current at $-V_{CE}$ = 50 V		CEO	-	500	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 6 V					

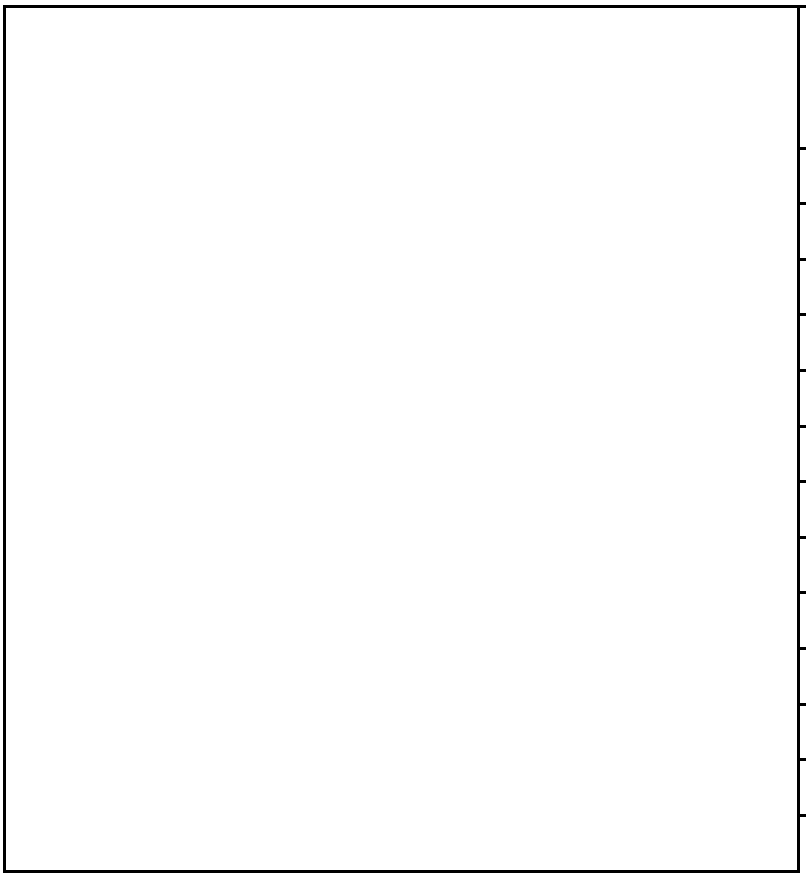
MU

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23			

Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices),YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website https://www.yfwdiode.com, or consult YFW sales office for further assistance.